

Abstract

The subject of the present invention is to reduce micro scratches by applying chemical-mechanical polishing. A polishing slurry is diluted with deionized water immediately before it is supplied in a gap between a polishing pad and the surface to be polished of a wafer. By diluting the polishing slurry with deionized water to increase its volume, the concentration of coagulated particles contained in the polishing slurry can be lowered. For a mixture ratio of the polishing slurry and deionized water, about 1 (polishing slurry): 1 - 1.2 (deionized water) is used and the concentration of silica contained in the diluted polishing slurry is adjusted to about 3 - 9 weight %, preferably about 4 - 8 weight % and more preferably about 8 weight %.